

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|--|------------------|---------|------------------|
| L14 | 332 | (MOS NMOS PMOS CMOS MOSFET) and memory adj array and (poly adj Si polysilicon) near3 gate and ("SiO.sub.2" silicon adj (oxide dioxide)) near3 gate adj (dielectric insulator insulating) and (RAM DRAM SRAM) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/26 11:53 |
| L15 | 82 | L14 and (@ad<"20000628" @rlad<"20000628") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/26 11:53 |
| S42 | 39 | ("3849204" "3923559" "4027380" "4113514" "4151007" "4212100" "4239554" "4290825" "4331486" "4352835" "4435896" "4542512" "4620211" "4796081" "4936781" "4962065" "4992840" "5059551" "5162892" "5179029" "5198880" "5248348" "5250446" "5254506" "5264724" "5320975" "5434440" "5514628" "5571339" "5693961" "5711998" "5744202" "5822175" "5830575" "5864161" "5872387" "6023093" "6147014" "6328801").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2008/03/25 11:14 |
| S43 | 2 | ("6147014").PN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/03/25 12:13 |
| S44 | 177 | MOSFET and gate near3 (poly polysilicon) and gate adj ((dielectric insulator) near2 (oxide silicon adj oxide SiO "SiO.sub.2" "SiO.sub.x") oxide) same (PECVD plasma adj CVD) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:30 |

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| S45 | 94 | S44 and (@ad<"20000628" @rlad<"20000628") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:32 |
| S46 | 37 | MOSFET and gate near3 (poly polysilicon) and gate adj ((dielectric insulator) near2 (oxide silicon adj oxide SiO "SiO.sub.2" "SiO.sub.x") oxide) with (PECVD plasma adj CVD) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:34 |
| S47 | 19 | S46 and (@ad<"20000628" @rlad<"20000628") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:35 |
| S48 | 15 | ("4141022" "5413948" "5607872" "5658813" "5739549" "5956579" "5981365" "6022765" "6037197" "6080606" "6118139" "6133073" "6146928" "6191017" "6210998").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2008/03/25 12:51 |
| S49 | 8 | (257/E21.489).CCLS. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/03/25 12:55 |
| S50 | 0 | (257/E21.491).CCLS. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/03/25 12:55 |
| S51 | 4 | kauffman same (SiO silicon adj (dioxide oxide)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S52 | 14 | kauffman and MOSFET and (SiO silicon adj (dioxide oxide)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |

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| S53 | 120 | MOSFET and (hydrogen H) adj2 ion same (SiO silicon adj (dioxide oxide)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S54 | 155 | MOSFET and (hydrogen H) adj2 ion same (SiO gate adj oxide silicon adj (dioxide oxide)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S55 | 63 | S54 and (@ad<"20000628" @rlad<"20000628") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S56 | 33 | kauffman adj ion | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S57 | 1122 | (hydrogen H) adj2 ion same (SiO gate adj oxide silicon adj (dioxide oxide)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S58 | 523 | S57 and (@ad<"20000628" @rlad<"20000628") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S59 | 437 | (hydrogen H) adj2 ion with (SiO gate adj oxide silicon adj (dioxide oxide)) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S60 | 256 | S59 and (@ad<"20000628" @rlad<"20000628") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S61 | 182 | (438/FOR.448).OCLS. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/03/25 12:55 |

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| S62 | 0 | (438/ FOR448).CCLS. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/03/25 12:55 |
| S63 | 180 | S61 and (@ad<"20000628" @rlad<"20000628") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S64 | 39 | ((hydrogen H) adj2 ion "H. sup.+ " "H.sup.2+") near6 plasma same (SiO gate adj oxide silicon adj (dioxide oxide)) and (gate MOSFET FET) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S65 | 22 | S64 and (@ad<"20000628" @rlad<"20000628") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |
| S66 | 28 | (david near3 chapek).in. | US-PGPUB; USPAT; USOCR | OR | ON | 2008/03/25 12:55 |
| S67 | 304 | (257/E21.212).CCLS. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/03/25 12:55 |
| S68 | 509 | (438/798).CCLS. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/03/25 12:55 |
| S69 | 459 | (438/783).CCLS. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/03/25 12:55 |
| S70 | 177 | S67 and (@ad<"20000628" @rlad<"20000628") | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/25 12:55 |

3/ 26/ 2008 12:28:04 PM

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